

### In the Specification

~ Please change the title to --Method For Testing Semiconductor Wafers--

~ On page 2, line 1, add the following:

#### 1-Cross Reference To Related Applications

4-1 This application is a division of application serial no. 09/929,388, filed August 14, 2001, which is a division of application serial no. 09/303,367 filed April 30, 1999, Patent No. 6,275,052, which is a division of application serial no. 08/797,719 filed February 11, 1997, Patent No. 6,060,891.

Please substitute the following clean replacement paragraph for the last paragraph on page 29 (page 29, line 29 to page 30, line 5).

P-2  
7- Following blanket deposition of the desired conductive metal, a resist mask can be formed and used for etching the conductive metal such that at least a portion of the contact members 20 remain covered with the conductive layers 52. The resist mask can be deposited using a standard photoresist deposition and exposure process. This can include spin deposition, followed by hardening, exposure and development. U.S. Patent Application Serial No. 08/520,871, now U.S. Patent No. 5,607,818, incorporated herein by reference describes a method for patterning a conductive layer using an electrophoretically deposited layer of resist.